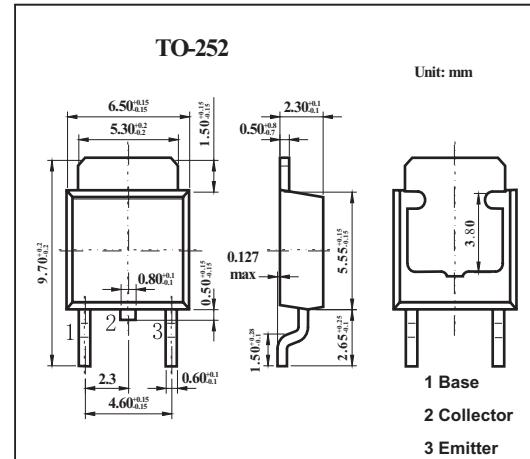


High-Voltage Switching Applications

2SC4134

■ Features

- High breakdown voltage and large current capacity.
- Fast switching speed.

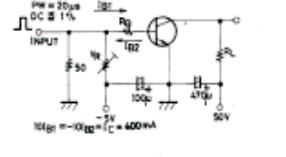


■ Absolute Maximum Ratings Ta = 25°C

Parameter	Symbol	Rating	Unit
Collector-base voltage	V _{CBO}	-120	V
Collector-emitter voltage	V _{CEO}	-100	V
Emitter-base voltage	V _{EBO}	-6	V
Collector current	I _C	-1	A
Collector current (pulse)	I _{CP}	-2	A
Collector dissipation	P _C	0.8	W
Collector dissipation T _c =25°C	P _C	10	W
Junction temperature	T _j	150	°C
Storage temperature	T _{stg}	-55 to +150	°C

2SC4134

■ Electrical Characteristics Ta = 25°C

Parameter	Symbol	Testconditons	Min	Typ	Max	Unit
Collector cutoff current	I _{CBO}	V _{CB} = 100V, I _E =0			100	nA
Emitter cutoff current	I _{EBO}	V _{EB} = 4V, I _C =0			100	nA
DC current gain	h _{FE}	V _{CE} =5V , I _C = 100mA	100		400	
Gain bandwidth product	f _T	V _{CE} = 10V , I _C = 100mA	120			MHz
Output capacitance	C _{OB}	V _{CB} = 10V , f = 1.0MHz	8.5			pF
Collector-emitter saturation voltage	V _{CES(sat)}	I _C = 400mA , I _B = 40mA	0.1	0.4		V
Base-emitter saturation voltage	V _{BE(sat)}	I _C = 400mA , I _B = 40mA	0.85	1.2		V
Collector-base breakdown voltage	V _{(BR)CBO}	I _C = 10μA , I _E = 0	120			V
Collector-emitter breakdown voltage	V _{(BR)CEO}	I _C = 1mA , R _{BE} = ∞	100			V
Emitter-base breakdown voltage	V _{(BR)EBO}	I _E = 10μA , I _C = 0	6			V
Turn-on time	t _{on}	 Unit (resistance : Ω, capacitance : F) (For PNP, the polarity is reversed.)		80		ns
Storage time	t _{stg}			850		ns
Fall time	t _f			50		ns

■ hFE Classification

Rank	R	S	T
hFE	100~200	140~280	200~400